

MEMORY CELL STRINGS IN A RESISTIVE CROSS POINT MEMORY CELL ARRAY

Abstract of the Disclosure

A method for performing a read operation from a memory cell in a memory cell string is provided. The method includes applying a constant current across the memory cell string, measuring a first voltage across the memory cell string, writing the memory cell to a first state, measuring a second voltage across the memory cell string, and determining whether the first voltage differs from the second voltage.